PERSISTENT CURRENTS IN 1D DISORDERED RINGS OF INTERACTING ELECTRONS

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We calculate the persistent current of 1D rings of spinless ferm ions with shortrange interactions on a lattice with up to 20 sites, and in the presence of disorder, for various band llings. We nd that both disorder and interactions always decrease the persistent current by localizing the electrons. Away from half-lling, the interaction has a much stronger in uence in the presence of disorder than in the pure case.

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The recent discovery of persistent currents in m esoscopic rings has addressed new interesting questions on the therm odynam ics of these system s. A lthough such an e ect was predicted for a long time, the unexpectedly large amplitude of the measured currents lead to important interrogations. Am ong them, the role of e-e interactions is still unclear. It has been proposed [1] that the interactions contribute to the average current which is measured in a many rings experiments [2]. On the other hand, the importance of the choice of the statistical ensemble to calculate average values has also been stressed [3]. A lthough the rst explanation, based on a perturbative calculation both in interaction and disorder, seem s to give a quantitative estimate closer to the experiment, it is still too small by one order of magnitude and the interaction parameter used in the theory is not well known.

In addition, for a single ring experim ent [4], the magnitude of the measured current is also not understood and, up to now, perturbation theory has failed to explain an enhancement of the current [5]. It is only when disorder is weaker that experiment and theory seem to agree [6], even for non interacting electrons.

At the moment, the role of the interactions in disordered systems is still unclear and the subject is vastly open. It has been recently proposed that, in the presence of interactions, the current should be larger than for free electrons, the electron of the interactions being to counteract the disorder electron electron.

The aim of this paper is to describe the interplay between the interactions and the disorder on the persistent currents in 1D rings. We choose a model of spinless ferm ions with short range interactions on a lattice. Our main result is that a repulsive interaction always decreases the amplitude of the current. It is well known that the 1D description is certainly not the most appropriate one to describe quantitatively experiments which are performed in rings with nite width, in the di usive regime. But our hope is to nd numerical results which may give indications for a more real situation.

We describe a chain of 1D spinless ferm ions in the presence of disorder with the following Hamiltonian:

$$H = t = 2 \sum_{i}^{X} (exp (2i = N) c_{i}^{Y} c_{i+1} + hx:) + V \sum_{i}^{X} n_{i} n_{i+1} + \sum_{i}^{X} w_{i} n_{i}$$
(0.1)

where w_i are on-site energies and are chosen random by between -W /2 and W /2 and V is

0

the nearest neighbour C oulom b repulsion. In the following we will take t=1, is the total magnetic ux through the ring (measured in units of ux quantum $_0 = h=e$) and N is the number of sites. (We use the conventional notation for the amplitude of disorder W and for the nearest neighbors interaction V. These notations are opposite to those used in ref. [7]).

Let us not recall some physical properties of this ham iltonian without disorder, i.e. W = 0. In one dimension, for repulsive interaction, a metal-insulator transistion occurs at half-lling due to the existence of um klapp processes. However away from half-lling, the um klapp processes become irrelevant and the system is expected to be metallic [8]. For Ham iltonian (0.1), the metal-insulator (M ott) transition occurs at V=1. The system is insulator for V > 1 and metallic for 0 V < 1.

This transition can also be described in the spin picture [8]. In the case W = 0, the model is integrable and is form ally equivalent to an anisotropic spin model, as obtained by a standard W igner-Jordan transform ation. By this way the new Ham iltonian reads:

$$H_{X X Z} = t = 2 \sum_{i}^{X} (\exp(2i = N) S_{i}^{+} S_{i+1} + hc:) + V [N = 4 + \sum_{i}^{X} S_{i+1}^{z} S_{i+1}^{z}]$$
(0.2)

For the XXZ model, V = 1 corresponds to a transition from an XY-model (V < 1) to an Ising model (V > 1). V = 1 corresponds to an isotropic Heisenberg system. Note that a spin gap opens up for V > 1. It corresponds to the gap in the charge excitations for Ham iltonian (0.1) characteristic of the insulator. W ith disorder, W \in 0, we must add in (0.2), the following term

$$H_{random} = \sum_{i}^{X} w_{i} (S_{i}^{z} = 1=2)$$
 (0.3)

This term describes the interaction of the local spins with random magnetic elds.

We now turn to the numerical calculation of the ground state energy as a function of the total magnetic ux E () which is the rst step of our work. The ground state energy is obtained from a standard Lanczos algorithm [9]. First of all, let us brie y describe som e technical aspects of the method. The calculation is limited to relatively small system sizes N, since (i) the H ilbert space dimension grows exponentially fast with N, (ii) we have to average over many realizations of the disorder, (because of statistical uctuations) and (iii) the disorder breaks the translation symmetry. The system sizes we were interested in, vary from 6 to 20 sites and we have chosen to consider two di erent cases: half and quarter llings. Let us rem ind that the Lanczos m ethod consists in the construction of a tridiagonal m atrix by applying iteratively the H am iltonian on an initial random vector. By this way a basis of norm alized vectors $_n$ is de ned as well as a set of values e_n and b_n given by the relationship, $H_n = b_{n,1} + e_{n,n} + b_{n+1} + h_{n+1}$. Hence we construct by iteration a tridiagonal H am iltonian m atrix expressed in the $_n$ basis that we diagonalize to obtain the spectrum of the eigenvalues. This kind of process is rapidly converging.

Let us, now, consider the calculation of the persistent current in such rings threaded by a total ux . A susual the current is de ned by

$$I() = \frac{1}{2} \frac{0 E()}{0}; \qquad (0.4)$$

where E () is calculated by exact diagonalization of the Ham iltonian. A swell known, the ux can be gauged out from the Ham iltonian so that the presence of an Aharonov-Bohm ux through a ring is analogous to a twist in the boundary conditions $(x + N) = (x)e^{2i}$. The spectrum and the persistent current have the ux periodicity of one.

In gs1,2, I() is plotted versus for a 16 site ring at electron density < n > = 0.5and < n > = 0.25 in (a) and (b) respectively, for di erent values of the disorder and the interaction. Fig.1 corresponds to the 'ordered' interacting case W = 0 and disorder W = 0.5is introduced in g2.0n g1, a discontinuity of I() appears at = 0, for zero disorder (W = 0). Indeed, in the absence of disorder, translation symmetry is preserved and total momentum is a good quantum number. As a function of , a crossing occurs between two lowest energy levels with dierent momenta. This crossing occurs at = 0 for an even number of electrons or at = 0.5 for an odd number. This can be easily understood in $(n_{2E(n)}) \cos(k_n + 2) = N$) and the subset of the non interacting case where E() =the electron momenta $k_n = 2$ n=N is chosen in order to minimize the total energy. Since translation invariance is preserved in the presence of interactions, the discontinuity still exists for nite V.W hen disorder is introduced (W \in 0) in g2, the scattering potential lifts the degeneracy at the crossing point and hence leads to a continuous variation of the current. In g.1a (half-lling) we clearly observe the e ect of the M ott transition on the currents: we notice that for V < 1, I is slowly varying with V, but when V > 1 a drop of the current

appears. However, away from half-lling (see g.lb), the current is not a ected form oderate interactions. At W = 0 and away from half-lling, the system is always metallic.

In gs2a and b, the in wence of the repulsive interaction is shown for a xed in purity potential of magnitude W = 0.5 and for the same parameters as in gs.1 (N = 16, < n > = 0.5 and < n > = 0.25). Clearly, in the half-lled case (g2a), the repulsion tends to suppress the current even further. This is reminicent of the M ott localization which occurs in the pure system. W ith increasing W, I() decreases as expected due to a stronger localization by the impurity potential. Such an elect has also been found in a ring of spinless fermions with long-range interactions [11].

M ore interesting is the e ect of the interaction away from half-lling where no localization is expected in the absence of disorder. A sseen previously in glb the e ect of the interaction for W = 0 is extremely weak, because of the absence of Um klapp scattering. However, it is clear from g2b that the interaction is much more e ective in the presence of the disorder $(W \neq 0)$; while on glb V had alm ost no e ect, in g2b, for a relatively weak disorder, V leads to a signi cant decrease of the current. Such a striking in uence of the interaction V is also seen in the metallic regime at half-lling (compare e.g. V = 0 and 1 in gs.la and 2a).

At this point, we would like to describe more qualitatively the transition from the localized regime (insulator) to the ballistic one (perfect m etal). As stressed by Scalapino and al. [12], the D rude weight D is a relevant parameter to characterize both of them. As originally noted by K ohn [13], the D rude weight D can be calculated from the dependence of the ground state energy versus ,

$$D = \frac{N}{4^{2}} \left(\frac{\theta^{2} E}{\theta^{2}} \right)_{= m} : \qquad (0.5)$$

where $_{m} = 0 \text{ or } 1/2$ is the location of the minimum of E (). As mentionned earlier, $_{m}$ depends on the parity of the number of electrons. For an even electron number parity, we take D as the second derivative at $_{m} = 1/2$.

Note that for free electrons $D = \langle n \rangle = m$ where $\langle n \rangle$ is the density of the mobile charge carriers and m = 1=2t is their mass. Generally D is given by [14]:

$$D = \frac{\langle n \rangle}{m}$$
(0.6)

where m is the elective mass of the carriers renormalized by the interaction. By this way, the D parameter can determ ine the dilerent regimes. A perfect metal (ballistic regime) will be caracterized by a nite value of D. This corresponds to a persistent current I scaling as 1=N. In the insulator, D vanishes exponentially as the size of the system goes to in nity, D / $e^{N=}$, where is the localization length. As a check of the numerical calculations on the drude peak, we observed the correct nite size scaling for W = 0, at half-lling D $_{lim}$ + a=N² for V < 1 and D / $e^{N=}$ for V > 1 when N > .

Since we consider disordered system s, we have to average over m any realizations of the disorder. The number of con gurations we averaged over vary from 50 to 250, depending on the size of the H ilbert space and the lling. In q.3 (< n > = 0.5) and q.4 (< n > = 0.25) D is plotted versus 1/N (N is the size of the ring). We rst consider the half-lled case (g.3). W hen V = 0 and W = 0, D goes to a nite value in the therm odynam ic limit (D $_{lim} = 1 =)$. As long as W = 0 (i.e. without disorder), the D rude weight is weakly a ected by a small interaction V < 1, signature that the system remains metallic. But for V > 1 (here V = 2) D decreases faster with N, the system becom es an insulator. W e now turn to the e ect of disorder. Once W € 0, we observe a tendancy towards localization for all V.W ith disorder in the system, the e ect of the interaction is also to increase the degree of localization. In the light of the results given by g.3 and 4, it appears that the role played by the interaction in presence of disorder (W \neq 0) is clearly different for < n >= 0.5 and for < n >= 0.25. On one hand, at < n > = 0.5 we see that the interaction V leads to a real decrease. For example, if we consider in q.3 the case W = 2 and compare the data for V = 0 and 2 we notice that the presence of the interaction reduces the localization length by more than a factor 3.0 n the other hand, at < n > = 0.25 (and xed W) the value of D is less a ected by the interaction V, as also observed on gs2a and 2b for the current. However, we note that the e ect of V is significantly larger for W \neq 0 than in the pure case W = 0. In summary, we do not observe any increase of D due to the competition between the interaction and the disorder.

We nish this paper by a few remarks on the conductivity spectrum. The optical con-

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ductivity is given by,

$$(!) = D (!) + _{req} (!)$$
 (0.7)

where $_{reg}$ (!) given by the K ubo form ula

$$_{\text{reg}}(!) = \frac{X}{N} \frac{j < m \, \text{fr} \, p > \text{f}}{E_{m} E_{0}} (! \quad (E_{m} E_{0}))$$
(0.8)

and j is the current density operator

$$\hat{j} = it = 2 \int_{i}^{X} (c_{i+1}^{v} c_{i+1} \exp(2i = N) hc)$$
 (0.9)

All quantities in (9) are calculated at = m and E_n are the excited m anybody energies. The amplitude D of the D nude (!) peak was calculated previously. We have explicitly checked the sum nule,

$$Z_{1}$$

(!)d! = (=2N) < 0 H_{kin} D (0.10)

where $< 0 H_{kin} D > is the groundstate expectation value of the kinetic energy.$

In g.5, (!) is plotted versus ! for a 16 site ring at half-lling, with V = 0.5 and for W = 0 or W = 1. In presence of the disorder we had averaged over 100 con gurations. We clearly see, as expected, that in the metallic case W = 0, the contribution at non zero frequency is negligeable (D 0.98 and only less than 1% of the weight is left at nite frequencies). However, when we introduce disorder, a strong absorption appears at non zero frequency with a peak around ! = 0.4t, while weight is removed from ! = 0 (D 0.52).

This broad absorption can be interpreted physically in the following way: if we assume that disorder localizes the wavefunctions in small nite size regions with a broad distribution of volumes, this leads to a correspondingly broad distribution of nite characteristic frequencies. In other words, the localized electrons can oscillate in disconnected regions of di erent sizes.

Let us sum m arize the m ain result of this paper. In our m odel for interacting electrons, we never observe an increase of the persistent current when interaction is switched on. At halflling, the interaction induces a m etal-insulator transition. The current strongly decreases, in qualitative agreement with the result of ref. [11]. Away from half-lling, the elect of the interaction is much weaker in the absence of disorder. However when impurity scattering exists, the interaction plays again a crucial role and leads to an additional decrease of the current. This is because it is more di cult to move correlated electrons in a random potential than independent electrons. Our results are in discrepancy with those of [7]. It will be of interest to know if the qualitative results obtained in this paper still apply for a multichannel ring.

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FIGURE CAPTIONS

Figure 1 Current I() versus for a 16 site ring at < n >= 0.5 (g.la) or at < n >= 0.25 (g.lb), xed V = 0 and W = 0,0.5 and 1. Figure 2 Current I() versus for a 16 site ring at < n >= 0.5 (g.2a) or < n >= 0.25 (g.2b), at xed W = 0 and V = 0, 1 and 2. Figure 3 Scaling of D at half-lling (< n >= 0.5). D vs 1/N for di erent V and W. Figure 4 Scaling of D at quarter lling (< n >= 0.25). Figure 5 Total conductivity (!) for a 16 site ring at < n >= 0.5 and (a) with or (b) without disorder (W = 0 and W = 1) for a xed V = 0.5. For W = 0 D 0.98. For W = 1, D_{aver:} 52 and we averaged over 100 realisations of the disorder.